imall

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ETR1119_003

Power MOSFET

■GENERAL DESCRIPTION

The XP151A13A0MR-G is an N-channel Power MOSFET with low on state resistance and ultra high-speed switching characteristics.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

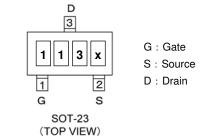
In order to counter static, a gate protect diode is built-in.

The small SOT-23 package makes high density mounting possible.

■ APPLICATIONS

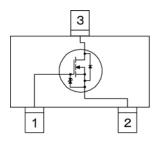
- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

■ PIN CONFIGURATION/ MARKING



* x represents production lot number.

■EQUIVALENT CIRCUIT



N-channel MOSFET (1 device built-in)

■FEATURES

Low On-State Resistance	: Rds(on) = 0.1 Ω@ Vgs = 4.5V
	: Rds(on) = 0.14Ω@ Vgs = 2.5V
	: Rds(on) = 0.25 Ω@ Vgs = 1.5V
Ultra High-Speed Switching	ng
Gate Protect Diode Built-i	in
Driving Voltage	: 1.5V
N-Channel Power MOSFE	T
DMOS Structure	
Small Package	: SOT-23
Environmentally Friendly	: EU RoHS Compliant, Pb Free

■ PRODUCT NAMES

PRODUCTS	PACKAGE	ORDER UNIT
XP151A13A0MR	SOT-23	3,000/Reel
XP151A13A0MR-G ^(*)	SOT-23	3,000/Reel

^(*) The "-G" suffix denotes Halogen and Antimony free as well as being fully RoHS compliant.

■ABSOLUTE MAXIMUM RATINGS

		Ta	= 25°C
PARAMETER	SYMBOL	RATINGS	UNITS
Drain - Source Voltage	Vdss	20	V
Gate - Source Voltage	Vgss	±8	V
Drain Current (DC)	ld	1	А
Drain Current (Pulse)	ldp	4	А
Reverse Drain Current	ldr	1	А
Channel Power Dissipation *	Pd	0.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55~150	°C

* When implemented on a ceramic PCB

■ ELECTRICAL CHARACTERISTICS

DC Characteristics

DC Characteristics					Т	a = 25°C
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	ldss	Vds= 20V, Vgs= 0V	-	-	10	μA
Gate-Source Leak Current	lgss	Vgs= \pm 8V, Vds= 0V	-	-	±10	μA
Gate-Source Cut-Off Voltage	Vgs(off)	ld= 1mA, Vds= 10V	0.5	-	1.2	V
Drain-Source On-State Resistance *1	Rds(on)	ld= 0.5A, Vgs= 4.5V	-	0.075	0.100	Ω
		ld= 0.5A, Vgs= 2.5V	-	0.10	0.14	Ω
		ld= 0.1A, Vgs= 1.5V	-	0.17	0.25	Ω
Forward Transfer Admittance *1	Yfs	ld= 0.5A, Vds= 10V	-	4.2	-	S
Body Drain Diode Forward Voltage	Vf	lf= 1A, Vgs= 0V	-	0.8	1.1	V

*1 Effective during pulse test.

Dynamic Characteristics

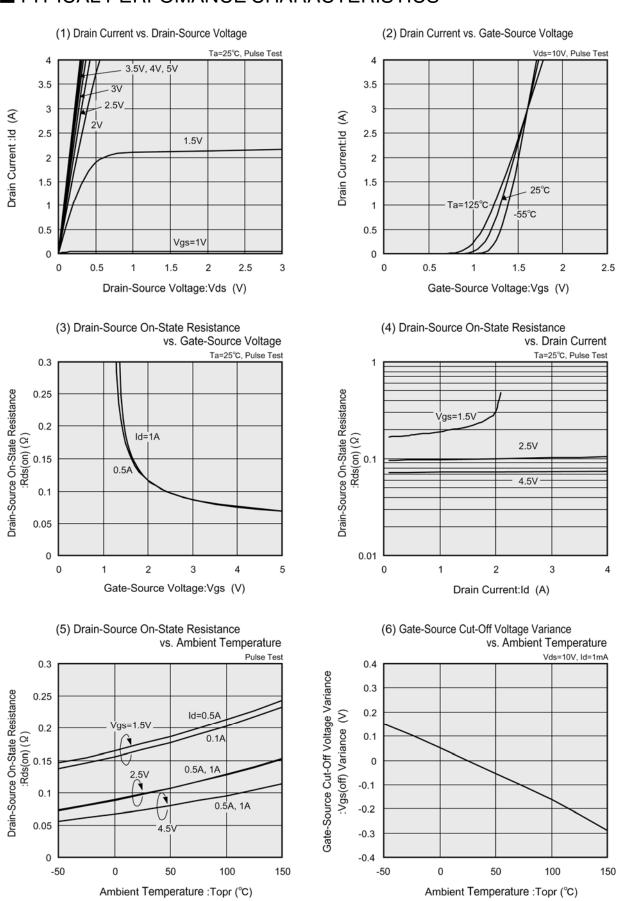
Dynamic Characteristics					Т	a = 25°C
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds= 10V, Vgs=0V f= 1MHz	-	220	-	pF
Output Capacitance	Coss		-	120	-	pF
Feedback Capacitance	Crss		-	45	-	pF

Switching Characteristics

Switching Characteristics					Т	a = 25°C
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs= 5V, Id= 0.5A Vdd= 10V	-	10	-	ns
Rise Time	tr		-	15	-	ns
Turn-Off Delay Time	td (off)		-	75	-	ns
Fall Time	tf		-	65	-	ns

Thermal Characteristics

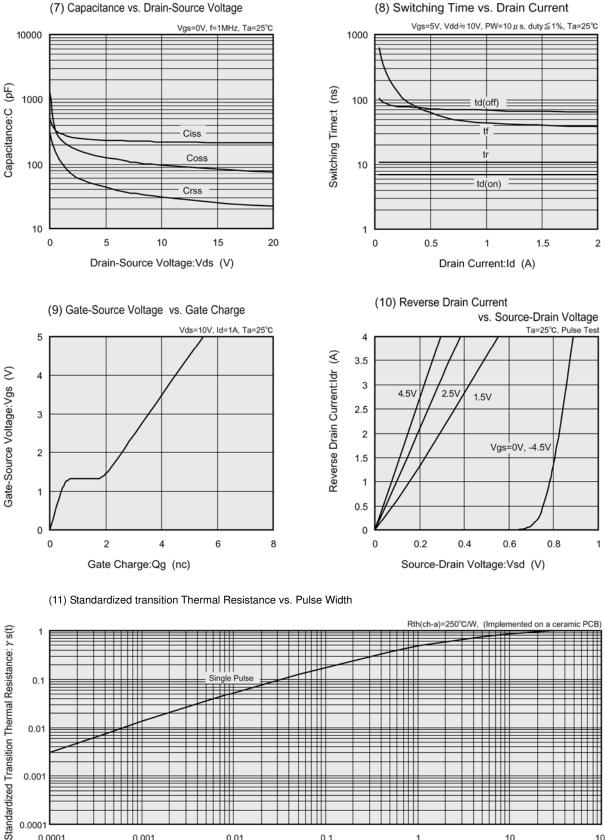
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	250	-	°C/W

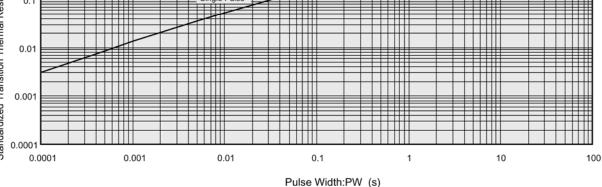


TYPICAL PERFOMANCE CHARACTERISTICS

TOIREX 3/5

■TYPICAL PERFOMANCE CHARACTERISTICS (Continued)





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